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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

-XF

Product Status	Obsolete
Core Processor	PIC
Core Size	8-Bit
Speed	10MHz
Connectivity	I ² C, SPI
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	1.75KB (1K x 14)
Program Memory Type	FLASH
EEPROM Size	128 x 8
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 5x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	18-SOIC (0.295", 7.50mm Width)
Supplier Device Package	18-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16lf818-i-sotsl

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

AddessBit 7Bit 6Bit 8Bit 4Bit 3Bit 2Bit 1Bit 0Value on page: page:10001INDFAddressAddressStatusS										1	1	1		
Bank 2 100h ¹⁰ <	Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value on POR, BOR	Details on page:		
1000 ¹⁰ INDF Addressing this location uses contents of FSR to address data memory (not a physical register) 0000 0.000 2.3 101h TIMRO Time0 Module Register 5.3 5.3 102h ¹⁰ PCL Program Counter's (PC) Least Significant Byte 0.000 0.000 2.3 103h ¹⁰ STATUS IRP RP1 RP0 TO PD Z DC C 0.001 1.802 2.3 103h ¹⁰ STATUS IRP RP1 RP0 TO PD Z DC C 0.01 1.802 2.3 103h ¹⁰ FTATUS Indirect Data Memory Address Pointer More Techne Memory Addr	Bank 2	Bank 2												
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1030 ⁽¹¹⁾ STATUSIRPRP1RP1RT0TOPDZDCC001 1xx141040 ⁽¹¹⁾ FSRIndire Jean Memory Jean Status107PDZDCC001 1xx231056PORTPOPRTPOPRTPIntime Jean StatusJean Status	102h ⁽¹	PCL	Program	Counter's (P	C) Least Sign	ificant Byte					0000 0000	23		
104h ⁰¹ FSRIndirect Data Memory Address Pointer90789078Unimplemented907890782000 2000907907106hPORTBPORTB Data Lath Werniter, PUTB pirster Net Verture, PUTB pirst	103h ⁽¹⁾	STATUS	IRP	RP1	RP0	TO	PD	Z	DC	С	0001 1xxx	16		
105hOr106hPORTBPORTB bata Lather witten; PORTB pins witten; PORTB p	104h ⁽¹⁾	FSR	Indirect D	ata Memory	Address Poir	iter					xxxx xxxx	23		
106nPORTBPORTBUNITUNITNAME	105h	_	Unimplen	nented							_	—		
1010ImageI	106h	PORTB	PORTB D	Data Latch w	hen written; P	ORTB pins w	hen read				xxxx xxxx	43		
10800000109400 <td>107h</td> <td>_</td> <td>Unimplen</td> <td>nented</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td>_</td> <td>—</td>	107h	_	Unimplen	nented							_	—		
109000	108h	_	Unimplen	nented							_	—		
10Ah ⁽¹⁾ 10B(1)Image <t< td=""><td>109h</td><td>_</td><td>Unimplen</td><td>nented</td><td></td><td></td><td></td><td></td><td></td><td></td><td>_</td><td>—</td></t<>	109h	_	Unimplen	nented							_	—		
1080 ⁽¹⁾ INTCONGEIPFIETMROIEINTROIINTROIFINTFRBIF0.00 0.000181000EEDATAEEPAUHSetan ExpertanceSetan Ray	10Ah ^(1,2)	PCLATH	—	_	_	Write Buffer	for the upper	5 bits of the F	Program Cou	nter	0 0000	23		
10ChEEDATAEEPROH-lish Jat wight	10Bh ⁽¹⁾	INTCON	GIE	PEIE	TMR0IE	INTE	RBIE	TMR0IF	INTF	RBIF	0000 000x	18		
10DnEADREXERNM/First Register/Joint	10Ch	EEDATA	EEPRON	1/Flash Data	Register Low	Byte					xxxx xxxx	25		
10EhEEDATHEEPROM/File> Lata Registre	10Dh	EEADR	EEPRON	1/Flash Addre	ess Register L	ow Byte					xxxx xxxx	25		
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188h — Unimplemented — — — — — — — — — 1233 189h — Unimplemented — — Model — Model — Model — Model — Model	187h	—	Unimplen	nented							_	_		
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18Fh — Reserved; maintain clear 0000 0000 —	18Eh	—	Reserved	l; maintain cl	ear						0000 0000	—		
	18Fh		Reserved	l; maintain cl	ear						0000 0000	_		

TABLE 2-1: SPECIAL FUNCTION REGISTER SUMMARY (CONTINUED)

Legend: x = unknown, u = unchanged, q = value depends on condition, - = unimplemented, read as '0', r = reserved.

Shaded locations are unimplemented, read as '0'. Note 1: These registers can be addressed from any bank.

2: The upper byte of the program counter is not directly accessible. PCLATH is a holding register for the PC<12:8>, whose contents are transferred to the upper byte of the program counter.

3: Pin 5 is an input only; the state of the TRISA5 bit has no effect and will always read '1'.

3.3 Reading Data EEPROM Memory

To read a data memory location, the user must write the address to the EEADR register, clear the EEPGD control bit (EECON1<7>) and then set control bit, RD (EECON1<0>). The data is available in the very next cycle in the EEDATA register; therefore, it can be read in the next instruction (see Example 3-1). EEDATA will hold this value until another read or until it is written to by the user (during a write operation).

The steps to reading the EEPROM data memory are:

- 1. Write the address to EEADR. Make sure that the address is not larger than the memory size of the device.
- 2. Clear the EEPGD bit to point to EEPROM data memory.
- 3. Set the RD bit to start the read operation.
- 4. Read the data from the EEDATA register.

		DA	• *	
BANKSEL	EEADR		;	Select Bank of EEADR
MOVF	ADDR, W		;	
MOVWF	EEADR		;	Data Memory Address
			;	to read
BANKSEL	EECON1		;	Select Bank of EECON1
BCF	EECON1,	EEPGD	;	Point to Data memory
BSF	EECON1,	RD	;	EE Read
BANKSEL	EEDATA		;	Select Bank of EEDATA
MOVF	EEDATA,	W	;	W = EEDATA

EXAMPLE 3-1: DATA EEPROM READ

3.4 Writing to Data EEPROM Memory

To write an EEPROM data location, the user must first write the address to the EEADR register and the data to the EEDATA register. Then, the user must follow a specific write sequence to initiate the write for each byte.

The write will not initiate if the write sequence is not exactly followed (write 55h to EECON2, write AAh to EECON2, then set WR bit) for each byte. We strongly recommend that interrupts be disabled during this code segment (see Example 3-2).

Additionally, the WREN bit in EECON1 must be set to enable write. This mechanism prevents accidental writes to data EEPROM due to errant (unexpected) code execution (i.e., lost programs). The user should keep the WREN bit clear at all times except when updating EEPROM. The WREN bit is not cleared by hardware

After a write sequence has been initiated, clearing the WREN bit will not affect this write cycle. The WR bit will be inhibited from being set unless the WREN bit is set. At the completion of the write cycle, the WR bit is cleared in hardware and the EE Write Complete Interrupt Flag bit (EEIF) is set. The user can either enable this interrupt or poll this bit. EEIF must be cleared by software.

The steps to write to EEPROM data memory are:

- 1. If step 10 is not implemented, check the WR bit to see if a write is in progress.
- 2. Write the address to EEADR. Make sure that the address is not larger than the memory size of the device.
- 3. Write the 8-bit data value to be programmed in the EEDATA register.
- 4. Clear the EEPGD bit to point to EEPROM data memory.
- 5. Set the WREN bit to enable program operations.
- 6. Disable interrupts (if enabled).
- 7. Execute the special five instruction sequence:
 - Write 55h to EECON2 in two steps (first to W, then to EECON2)
 - Write AAh to EECON2 in two steps (first to W, then to EECON2)
 - · Set the WR bit
- 8. Enable interrupts (if using interrupts).
- 9. Clear the WREN bit to disable program operations.
- 10. At the completion of the write cycle, the WR bit is cleared and the EEIF interrupt flag bit is set (EEIF must be cleared by firmware). If step 1 is not implemented, then firmware should check for EEIF to be set, or WR to be clear, to indicate the end of the program cycle.

EXAMPLE 3-2: DATA EEPROM WRITE

		BANKSEL	EECON1		;	Select Bank of
		BTFSC GOTO BANKSEL	EECON1, \$-1 EEADR	WR	; ; ; ;	Wait for write to complete Select Bank of
		MOVF	ADDR, W		; ;	EEADR
		MOAME	EEADR		; ;	Data Memory Address to write
		MOVF MOVWF	VALUE, V EEDATA	1	; ; ;	Data Memory Value
		BANKSEL	EECON1		;;;	Select Bank of EECON1
		BCF	EECON1,	EEPGD	;	Point to DATA
		BSF	EECON1,	WREN	; ;	Enable writes
		BCF MOVLW	INTCON, 55h	GIE	;;	Disable INTs.
ed	nce	MOVWF	EECON2		;	Write 55h
equir	enbe	MOVLW MOVWF	AAh EECON2		; ;	Write AAh
æ	ű	BSF	EECON1,	WR	;	Set WR bit to
L	•	BSF	INTCON,	GIE	; ;	Enable INTs.
		BCF	EECON1,	WREN	;	Disable writes

3.5 Reading Flash Program Memory

To read a program memory location, the user must write two bytes of the address to the EEADR and EEADRH registers, set the EEPGD control bit (EECON1<7>) and then set control bit, RD (EECON1<0>). Once the read control bit is set, the program memory Flash controller will use the second instruction cycle to read the data. This causes the second instruction immediately following the "BSF EECON1, RD" instruction to be ignored. The data is available in the very next cycle in the EEDATA and EEDATH registers; therefore, it can be read as two bytes in the following instructions. EEDATA and EEDATH registers will hold this value until another read or until it is written to by the user (during a write operation).

EXAMPLE 3-3:	FLASH PROGRAM READ

BANKSEL EEADRH		;	Select Bank of EEADRH
MOVF ADDRH,	W	;	
MOVWF EEADRH		;	MS Byte of Program
		;	Address to read
MOVF ADDRL,	W	;	
MOVWF EEADR		;	LS Byte of Program
		;	Address to read
BANKSEL EECON1		;	Select Bank of EECON1
BSF EECON1	, EEPGD	;	Point to PROGRAM
		;	memory
BSF EECON1	, RD	;	EE Read
		;	
NOP		;	Any instructions
		;	here are ignored as
NOP		;	program memory is
		;	read in second cycle
		;	after BSF EECON1,RD
BANKSEL EEDATA		;	Select Bank of EEDATA
MOVF EEDATA	, W	;	DATAL = EEDATA
MOVWF DATAL		;	
MOVF EEDATH	, W	;	DATAH = EEDATH
MOVWF DATAH		;	

3.6 Erasing Flash Program Memory

The minimum erase block is 32 words. Only through the use of an external programmer, or through ICSP control, can larger blocks of program memory be bulk erased. Word erase in the Flash array is not supported.

When initiating an erase sequence from the microcontroller itself, a block of 32 words of program memory is erased. The Most Significant 11 bits of the EEADRH:EEADR point to the block being erased. EEADR< 4:0> are ignored.

The EECON1 register commands the erase operation. The EEPGD bit must be set to point to the Flash program memory. The WREN bit must be set to enable write operations. The FREE bit is set to select an erase operation.

For protection, the write initiate sequence for EECON2 must be used.

After the "BSF EECON1, WR" instruction, the processor requires two cycles to set up the erase operation. The user must place two NOP instructions after the WR bit is set. The processor will halt internal operations for the typical 2 ms, only during the cycle in which the erase takes place. This is not Sleep mode, as the clocks and peripherals will continue to run. After the erase cycle, the processor will resume operation with the third instruction after the EECON1 write instruction.

3.6.1 FLASH PROGRAM MEMORY ERASE SEQUENCE

The sequence of events for erasing a block of internal program memory location is:

- 1. Load EEADRH:EEADR with address of row being erased.
- Set EEPGD bit to point to program memory; set WREN bit to enable writes and set FREE bit to enable the erase.
- 3. Disable interrupts.
- 4. Write 55h to EECON2.
- 5. Write AAh to EECON2.
- 6. Set the WR bit. This will begin the row erase cycle.
- 7. The CPU will stall for duration of the erase.



CERAMIC RESONATOR OPERATION (HS OR XT

OSC CONFIGURATION)



- **2:** A series resistor (Rs) may be required.
- 3: RF varies with the resonator chosen (typically between 2 M Ω to 10 M Ω).

TABLE 4-2: CERAMIC RESONATORS (FOR DESIGN GUIDANCE ONLY)

Typical Capacitor Values Used:									
Mode	Freq	OSC1	OSC2						
ХТ	455 kHz	56 pF	56 pF						
	2.0 MHz	47 pF	47 pF						
	4.0 MHz	33 pF	33 pF						
HS	8.0 MHz	27 pF	27 pF						
	16.0 MHz	22 pF	22 pF						

Capacitor values are for design guidance only.

These capacitors were tested with the resonators listed below for basic start-up and operation. These values were not optimized.

Different capacitor values may be required to produce acceptable oscillator operation. The user should test the performance of the oscillator over the expected VDD and temperature range for the application.

See the notes following this table for additional information.

Note: When using resonators with frequencies above 3.5 MHz, the use of HS mode rather than XT mode is recommended. HS mode may be used at any VDD for which the controller is rated. If HS is selected, it is possible that the gain of the oscillator will overdrive the resonator. Therefore, a series resistor should be placed between the OSC2 pin and the resonator. As a good starting point, the recommended value of Rs is 330Ω .

4.3 External Clock Input

The ECIO Oscillator mode requires an external clock source to be connected to the OSC1 pin. There is no oscillator start-up time required after a Power-on Reset or after an exit from Sleep mode.

In the ECIO Oscillator mode, the OSC2 pin becomes an additional general purpose I/O pin. The I/O pin becomes bit 6 of PORTA (RA6). Figure 4-3 shows the pin connections for the ECIO Oscillator mode.



EXTERNAL CLOCK INPUT OPERATION (ECIO CONFIGURATION)



4.4 RC Oscillator

For timing insensitive applications, the "RC" and "RCIO" device options offer additional cost savings. The RC oscillator frequency is a function of the supply voltage, the resistor (REXT) and capacitor (CEXT) values and the operating temperature. In addition to this, the oscillator frequency will vary from unit to unit due to normal manufacturing variation. Furthermore, the difference in lead frame capacitance between package types will also affect the oscillation frequency, especially for low CEXT values. The user also needs to take into account variation due to tolerance of external R and C components used. Figure 4-4 shows how the R/C combination is connected.

In the RC Oscillator mode, the oscillator frequency divided by 4 is available on the OSC2 pin. This signal may be used for test purposes or to synchronize other logic.





The RCIO Oscillator mode (Figure 4-5) functions like the RC mode except that the OSC2 pin becomes an additional general purpose I/O pin. The I/O pin becomes bit 6 of PORTA (RA6).

FIGURE 4-5: RCIO OSCILLATOR MODE



4.5 Internal Oscillator Block

The PIC16F818/819 devices include an internal oscillator block which generates two different clock signals; either can be used as the system's clock source. This can eliminate the need for external oscillator circuits on the OSC1 and/or OSC2 pins.

The main output (INTOSC) is an 8 MHz clock source which can be used to directly drive the system clock. It also drives the INTOSC postscaler which can provide a range of clock frequencies from 125 kHz to 4 MHz.

The other clock source is the internal RC oscillator (INTRC) which provides a 31.25 kHz (32 μs nominal period) output. The INTRC oscillator is enabled by selecting the INTRC as the system clock source or when any of the following are enabled:

- Power-up Timer
- Watchdog Timer

These features are discussed in greater detail in **Section 12.0 "Special Features of the CPU"**.

The clock source frequency (INTOSC direct, INTRC direct or INTOSC postscaler) is selected by configuring the IRCF bits of the OSCCON register (Register 4-2).

Note: Throughout this data sheet, when referring *specifically* to a generic clock source, the term "INTRC" may also be used to refer to the clock modes using the internal oscillator block. This is regardless of whether the actual frequency used is INTOSC (8 MHz), the INTOSC postscaler or INTRC (31.25 kHz).

4.5.1 INTRC MODES

Using the internal oscillator as the clock source can eliminate the need for up to two external oscillator pins, which can then be used for digital I/O. Two distinct configurations are available:

- In INTIO1 mode, the OSC2 pin outputs Fosc/4 while OSC1 functions as RA7 for digital input and output.
- In INTIO2 mode, OSC1 functions as RA7 and OSC2 functions as RA6, both for digital input and output.





9.3 PWM Mode

In Pulse-Width Modulation (PWM) mode, the CCP1 pin produces up to a 10-bit resolution PWM output. Since the CCP1 pin is multiplexed with the PORTB data latch, the TRISB<x> bit must be cleared to make the CCP1 pin an output.

Note:	Clearing the CCP1CON register will force
	the CCP1 PWM output latch to the default
	low level. This is not the PORTB I/O data
	latch.

Figure 9-3 shows a simplified block diagram of the CCP module in PWM mode.

For a step by step procedure on how to set up the CCP module for PWM operation, see **Section 9.3.3 "Setup for PWM Operation"**.

FIGURE 9-3: SIMPLIFIED PWM BLOCK DIAGRAM



A PWM output (Figure 9-4) has a time base (period) and a time that the output stays high (duty cycle). The frequency of the PWM is the inverse of the period (1/period).

FIGURE 9-4: PWM OUTPUT



9.3.1 PWM PERIOD

The PWM period is specified by writing to the PR2 register. The PWM period can be calculated using the following formula.

EQUATION 9-1:

 $PWM Period = [(PR2) + 1] \bullet 4 \bullet TOSC \bullet$ (TMR2 Prescale Value)

PWM frequency is defined as 1/[PWM period].

When TMR2 is equal to PR2, the following three events occur on the next increment cycle:

- TMR2 is cleared
- The CCP1 pin is set (exception: if PWM duty cycle = 0%, the CCP1 pin will not be set)
- The PWM duty cycle is latched from CCPR1L into CCPR1H



9.3.2 PWM DUTY CYCLE

The PWM duty cycle is specified by writing to the CCPR1L register and to the CCP1CON<5:4> bits. Up to 10-bit resolution is available. The CCPR1L contains the eight MSbs and the CCP1CON<5:4> contains the two LSbs. This 10-bit value is represented by CCPR1L:CCP1CON<5:4>. The following equation is used to calculate the PWM duty cycle in time.

EQUATION 9-2:

CCPR1L and CCP1CON<5:4> can be written to at any time but the duty cycle value is not latched into CCPR1H until after a match between PR2 and TMR2 occurs (i.e., the period is complete). In PWM mode, CCPR1H is a read-only register.

The CCPR1H register and a 2-bit internal latch are used to double-buffer the PWM duty cycle. This double-buffering is essential for glitchless PWM operation.

When the CCPR1H and 2-bit latch match TMR2, concatenated with an internal 2-bit Q clock or 2 bits of the TMR2 prescaler, the CCP1 pin is cleared.

11.2 Selecting the A/D Conversion Clock

The A/D conversion time per bit is defined as TAD. The A/D conversion requires 9.0 TAD per 10-bit conversion. The source of the A/D conversion clock is software selectable. The seven possible options for TAD are:

- 2 Tosc
- 4 Tosc
- 8 Tosc
- 16 Tosc
- 32 Tosc
- 64 Tosc
- Internal A/D module RC oscillator (2-6 μs)

For correct A/D conversions, the A/D conversion clock (TAD) must be selected to ensure a minimum TAD time as small as possible, but no less than 1.6 μ s and not greater than 6.4 μ s.

Table 11-1 shows the resultant TAD times derived from the device operating frequencies and the A/D clock source selected.

11.3 Configuring Analog Port Pins

The ADCON1 and TRISA registers control the operation of the A/D port pins. The port pins that are desired as analog inputs must have their corresponding TRIS bits set (input). If the TRIS bit is cleared (output), the digital output level (VOH or VOL) will be converted.

The A/D operation is independent of the state of the CHS<2:0> bits and the TRIS bits.

- Note 1: When reading the Port register, all pins configured as analog input channels will read as cleared (a low level). Pins configured as digital inputs will convert an analog input. Analog levels on a digitally configured input will not affect the conversion accuracy.
 - 2: Analog levels on any pin that is defined as a digital input (including the AN4:AN0 pins) may cause the input buffer to consume current out of the device specification.

TABLE 11-1: TAD VS. MAXIMUM DEVICE OPERATING FREQUENCIES (STANDARD DEVICES (F))

	Maximum Dovico Eroquonov			
Operation	ADCS<2>	ADCS<1:0>	Maximum Device Frequency	
2 Tosc	0	00	1.25 MHz	
4 Tosc	1	00	2.5 MHz	
8 Tosc	0	01	5 MHz	
16 Tosc	1	01	10 MHz	
32 Tosc	0	10	20 MHz	
64 Tosc	1	10	20 MHz	
RC ^(1,2,3)	Х	11	(Note 1)	

Note 1: The RC source has a typical TAD time of 4 μ s but can vary between 2-6 μ s.

2: When the device frequencies are greater than 1 MHz, the RC A/D conversion clock source is only recommended for Sleep operation.

3: For extended voltage devices (LF), please refer to Section 15.0 "Electrical Characteristics".

14.0 DEVELOPMENT SUPPORT

The PIC[®] microcontrollers and dsPIC[®] digital signal controllers are supported with a full range of software and hardware development tools:

- Integrated Development Environment
- MPLAB[®] IDE Software
- Compilers/Assemblers/Linkers
 - MPLAB C Compiler for Various Device Families
 - HI-TECH C[®] for Various Device Families
 - MPASM[™] Assembler
 - MPLINK[™] Object Linker/ MPLIB[™] Object Librarian
 - MPLAB Assembler/Linker/Librarian for Various Device Families
- Simulators
 - MPLAB SIM Software Simulator
- Emulators
 - MPLAB REAL ICE™ In-Circuit Emulator
- In-Circuit Debuggers
 - MPLAB ICD 3
 - PICkit[™] 3 Debug Express
- Device Programmers
 - PICkit[™] 2 Programmer
 - MPLAB PM3 Device Programmer
- Low-Cost Demonstration/Development Boards, Evaluation Kits, and Starter Kits

14.1 MPLAB Integrated Development Environment Software

The MPLAB IDE software brings an ease of software development previously unseen in the 8/16/32-bit microcontroller market. The MPLAB IDE is a Windows[®] operating system-based application that contains:

- A single graphical interface to all debugging tools
 - Simulator
 - Programmer (sold separately)
 - In-Circuit Emulator (sold separately)
 - In-Circuit Debugger (sold separately)
- · A full-featured editor with color-coded context
- A multiple project manager
- Customizable data windows with direct edit of contents
- High-level source code debugging
- Mouse over variable inspection
- Drag and drop variables from source to watch windows
- Extensive on-line help
- Integration of select third party tools, such as IAR C Compilers

The MPLAB IDE allows you to:

- Edit your source files (either C or assembly)
- One-touch compile or assemble, and download to emulator and simulator tools (automatically updates all project information)
- Debug using:
 - Source files (C or assembly)
 - Mixed C and assembly
 - Machine code

MPLAB IDE supports multiple debugging tools in a single development paradigm, from the cost-effective simulators, through low-cost in-circuit debuggers, to full-featured emulators. This eliminates the learning curve when upgrading to tools with increased flexibility and power.

PIC16F818/819







15.2 DC Characteristics: Power-Down and Supply Current PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

PIC16LF8 (Indus	818/819 strial)	Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial							
PIC16F8 ⁴ (Indus	Standa Operati	$\begin{array}{ll} \mbox{Standard Operating Conditions (unless otherwise stated)} \\ \mbox{Operating temperature} & -40^{\circ}C \leq TA \leq +85^{\circ}C \mbox{ for industrial} \\ -40^{\circ}C \leq TA \leq +125^{\circ}C \mbox{ for extended} \end{array}$							
Param No.	Device	Тур	Max	Units	Conditions				
	Supply Current (IDD) ^(2,3)								
	PIC16LF818/819	9	20	μΑ	-40°C				
		7	15	μA	+25°C	VDD = 2.0V			
		7	15	μA	+85°C				
	PIC16LF818/819	16	30	μA	-40°C				
		14	25	μA	+25°C	VDD = 3.0V	Fosc = 32 kHz		
		14	25	μA	+85°C		(LP Oscillator)		
	All devices	32	40	μA	-40°C				
		26	35	μA	+25°C				
		26	35	μA	+85°C	vuu ≅ 5.0v			
	Extended devices	35	53	μΑ	+125°C				

Legend: Shading of rows is to assist in readability of the table.

Note 1: The power-down current in Sleep mode does not depend on the oscillator type. Power-down current is measured with the part in Sleep mode, with all I/O pins in high-impedance state and tied to VDD or VSS and all features that add delta current disabled (such as WDT, Timer1 Oscillator, BOR, etc.).

2: The supply current is mainly a function of operating voltage, frequency and mode. Other factors, such as I/O pin loading and switching rate, oscillator type and circuit, internal code execution pattern and temperature, also have an impact on the current consumption.

The test conditions for all IDD measurements in active operation mode are:

OSC1 = external square wave, from rail-to-rail; all I/O pins tri-stated, pulled to VDD;

MCLR = VDD; WDT enabled/disabled as specified.

3: For RC oscillator configurations, current through REXT is not included. The current through the resistor can be estimated by the formula Ir = VDD/2REXT (mA) with REXT in k Ω .

15.2 DC Characteristics: Power-Down and Supply Current PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

PIC16LF8 (Indus	818/819 strial)	Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial						
PIC16F8 ² (Indus	$ \begin{array}{llllllllllllllllllllllllllllllllllll$							
Param No.	Device	Тур	Max	Units		Condi	ions	
D022	Module Differential Currer	nts (∆lw	от, ∆Іво	R, ∆ILVD	, Δ IOSCB, Δ IAD)			
(∆IWDT)	Watchdog Timer	1.5	3.8	μΑ	-40°C			
		2.2	3.8	μΑ	+25°C	VDD = 2.0V		
		2.7	4.0	μA	+85°C			
		2.3	4.6	μA	-40°C			
		2.7	4.6	μA	+25°C	VDD = 3.0V		
		3.1	4.8	μΑ	+85°C			
		3.0	10.0	μΑ	-40°C	Vdd = 5.0V		
		3.3	10.0	μA	+25°C			
		3.9	13.0	μΑ	+85°C			
	Extended Devices	5.0	21.0	μΑ	+125°C			
D022A (∆IBOR)	Brown-out Reset	40	60	μΑ	-40°C to +85°C	VDD = 5.0V		
D025	Timer1 Oscillator	1.7	2.3	μΑ	-40°C			
(∆IOSCB)		1.8	2.3	μA	+25°C	VDD = 2.0V		
		2.0	2.3	μA	+85°C			
		2.2	3.8	μΑ	-40°C			
		2.6	3.8	μΑ	+25°C	VDD = 3.0V	32 kHz on Timer1	
		2.9	3.8	μΑ	+85°C			
		3.0	6.0	μΑ	-40°C			
		3.2	6.0	μΑ	+25°C	VDD = 5.0V		
		3.4	7.0	μΑ	+85°C			
D026	A/D Converter	0.001	2.0	μΑ	-40°C to +85°C	VDD = 2.0V		
(∆IAD)		0.001	2.0	μΑ	-40°C to +85°C	VDD = 3.0V	A/D on Sleep not converting	
		0.003	2.0	μA	-40°C to +85°C		A/D on, Sleep, not converting	
	Extended Devices	4.0	8.0	μA	-40°C to +125°C	v D.0 - 0.0 v		

Legend: Shading of rows is to assist in readability of the table.

Note 1: The power-down current in Sleep mode does not depend on the oscillator type. Power-down current is measured with the part in Sleep mode, with all I/O pins in high-impedance state and tied to VDD or VSS and all features that add delta current disabled (such as WDT, Timer1 Oscillator, BOR, etc.).

2: The supply current is mainly a function of operating voltage, frequency and mode. Other factors, such as I/O pin loading and switching rate, oscillator type and circuit, internal code execution pattern and temperature, also have an impact on the current consumption.

The test conditions for all IDD measurements in active operation mode are:

OSC1 = external square wave, from rail-to-rail; all I/O pins tri-stated, pulled to VDD;

MCLR = VDD; WDT enabled/disabled as specified.

3: For RC oscillator configurations, current through REXT is not included. The current through the resistor can be estimated by the formula Ir = VDD/2REXT (mA) with REXT in kΩ.

15.4 DC Characteristics: PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial)

DC CHARACTERISTICS			$\begin{array}{llllllllllllllllllllllllllllllllllll$					
Param No.	Sym	Characteristic	Conditions					
-	VIL	Input Low Voltage						
		I/O ports:						
D030		with TTL buffer	Vss	—	0.15 Vdd	V	For entire VDD range	
D030A			Vss	—	0.8V	V	$4.5V \leq V\text{DD} \leq 5.5V$	
D031		with Schmitt Trigger buffer	Vss	—	0.2 Vdd	V		
D032		MCLR, OSC1 (in RC mode)	Vss	—	0.2 Vdd	V	(Note 1)	
D033		OSC1 (in XT and LP mode)	Vss	—	0.3V	V		
		OSC1 (in HS mode)	Vss	—	0.3 Vdd	V		
		Ports RB1 and RB4:						
D034		with Schmitt Trigger buffer	Vss	—	0.3 Vdd	V	For entire VDD range	
	Vih	Input High Voltage						
		I/O ports:						
D040		with TTL buffer	2.0	—	Vdd	V	$4.5V \le VDD \le 5.5V$	
D040A			0.25 VDD + 0.8V	—	Vdd	V	For entire VDD range	
D041		with Schmitt Trigger buffer	0.8 Vdd	—	Vdd	V	For entire VDD range	
D042		MCLR	0.8 Vdd	—	Vdd	V		
D042A		OSC1 (in XT and LP mode)	1.6V	—	Vdd	V		
		OSC1 (in HS mode)	0.7 Vdd	—	Vdd	V		
D043		OSC1 (in RC mode)	0.9 Vdd	—	Vdd	V	(Note 1)	
		Ports RB1 and RB4:						
D044		with Schmitt Trigger buffer	0.7 Vdd	—	Vdd	V	For entire VDD range	
D070	IPURB	PORTB Weak Pull-up Current	50	250	400	μΑ	VDD = 5V, VPIN = VSS	
	lı∟	Input Leakage Current (Notes	I					
D060		I/O ports	—	—	±1	μA	Vss \leq VPIN \leq VDD, pin at high-impedance	
D061		MCLR	—	—	±5	μΑ	$Vss \leq V \text{PIN} \leq V \text{DD}$	
D063		OSC1	_	_	±5	μA	Vss \leq VPIN \leq VDD, XT, HS and LP oscillator configuration	

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: In RC oscillator configuration, the OSC1/CLKI pin is a Schmitt Trigger input. It is not recommended that the PIC16F818/819 be driven with external clock in RC mode.

- 2: The leakage current on the MCLR pin is strongly dependent on the applied voltage level. The specified levels represent normal operating conditions. Higher leakage current may be measured at different input voltages.
- 3: Negative current is defined as current sourced by the pin.



FIGURE 15-10: SPI MASTER MODE TIMING (CKE = 0, SMP = 0)

FIGURE 15-11: SPI MASTER MODE TIMING (CKE = 1, SMP = 1)









Param. No.	Symbol	Characteristic		Min	Мах	Units	Conditions
100*	Тнідн	Clock High Time	100 kHz mode	4.0	—	μs	
			400 kHz mode	0.6	—	μs	
			SSP Module	1.5 TCY	—		
101*	TLOW	Clock Low Time	100 kHz mode	4.7	—	μs	
			400 kHz mode	1.3	_	μs	
			SSP Module	1.5 TCY	_		
102*	TR	SDA and SCL Rise Time	100 kHz mode	—	1000	ns	
			400 kHz mode	20 + 0.1 Св	300	ns	CB is specified to be from 10-400 pF
103*	TF	SDA and SCL Fall Time	100 kHz mode	—	300	ns	
			400 kHz mode	20 + 0.1 Св	300	ns	CB is specified to be from 10-400 pF
90*	TSU:STA	Start Condition Setup Time	100 kHz mode	4.7	—	μs	Only relevant for Repeated Start condition
			400 kHz mode	0.6	_	μs	
91*	THD:STA	Start Condition Hold Time	100 kHz mode	4.0	—	μs	After this period, the first clock pulse is generated
			400 kHz mode	0.6	_	μS	
106*	THD:DAT	Data Input Hold Time	100 kHz mode	0	_	ns	
			400 kHz mode	0	0.9	μS	
107*	TSU:DAT	Data Input Setup Time	100 kHz mode	250	_	ns	(Note 2)
			400 kHz mode	100	—	ns	
92*	Tsu:sto	Stop Condition Setup Time	100 kHz mode	4.7	—	μS	
			400 kHz mode	0.6	—	μs	
109*	ΤΑΑ	Output Valid from Clock	100 kHz mode	—	3500	ns	(Note 1)
			400 kHz mode	—	—	ns	
110*	TBUF	Bus Free Time	100 kHz mode	4.7	—	μs	Time the bus must be free
			400 kHz mode	1.3		μs	before a new transmission can start
	Св	Bus Capacitive Loading		_	400	pF	

TABLE 15-8: I²C™ BUS DATA REQUIREMENTS

* These parameters are characterized but not tested.

Note 1: As a transmitter, the device must provide this internal minimum delay time to bridge the undefined region (min. 300 ns) of the falling edge of SCL to avoid unintended generation of Start or Stop conditions.

2: A Fast mode (400 kHz) I²CTM bus device can be used in a Standard mode (100 kHz) I²C bus system but the requirement, TSU:DAT ≥ 250 ns, must then be met. This will automatically be the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line, TR max. + TSU:DAT = 1000 + 250 = 1250 ns (according to the Standard mode I²C bus specification), before the SCL line is released.

PIC16F818/819









PIC16F818/819

NOTES:

18-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





Microchip Technology Drawing C04-051C Sheet 1 of 2

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